

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = +25^\circ C$
-20V	700mΩ @ $V_{GS} = -4.5V$	-460mA
	900mΩ @ $V_{GS} = -2.5V$	-420mA
	1300mΩ @ $V_{GS} = -1.8V$	-350mA

## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 3kV**
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

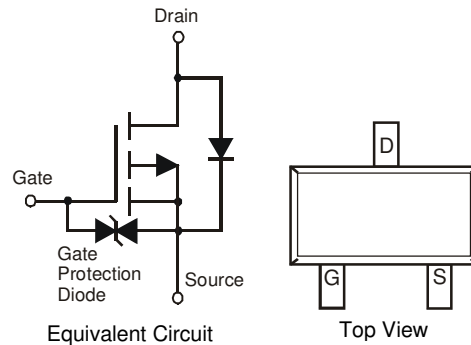
## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Load Switch
- Power Management Functions

## Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e3)</sup>
- Terminal Connections: See Diagram
- Weight: 0.002 grams (approximate)

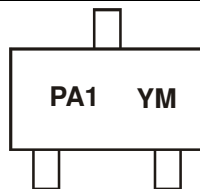


## Ordering Information (Note 3)

Part Number	Case	Packaging
DMG1013T-7	SOT523	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



PA1 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: W = 2009)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** @T<sub>A</sub> = +25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±6	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-0.46	A
		T <sub>A</sub> = +85°C		-0.33	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-6	A

**Thermal Characteristics** @T<sub>A</sub> = +25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			P <sub>D</sub>	0.27	W
Thermal Resistance, Junction to Ambient (Note 5)			R <sub>θJA</sub>	461	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = +25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-100	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±2.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-	0.5	0.7	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -350mA
			0.7	0.9		
			1.0	1.3		
Forward Transfer Admittance	Y <sub>fs</sub>	-	0.9	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA
Diode Forward Voltage	V <sub>SD</sub>	-	-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -150mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	-	59.76	-	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	12.07	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	6.36	-	pF	
Total Gate Charge	Q <sub>g</sub>	-	580	-	pC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA
Gate-Source Charge	Q <sub>gs</sub>	-	104	-	pC	
Gate-Drain Charge	Q <sub>gd</sub>	-	125	-	pC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω, I <sub>D</sub> = -200mA
Turn-On Rise Time	t <sub>r</sub>	-	8.1	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.4	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	20.7	-	ns	

- Notes:
5. For a device surface mounted on a minimum recommended pad layout of an FR4 PCB, in still air conditions; the device is measured when operating in steady-state condition.
  6. Same as note 5, except the device is pulsed at duty cycle of 1% for a pulse width of 10μs.
  7. Measured under pulsed conditions to minimize self-heating effect. Pulse width ≤ 300μs; duty cycle ≤ 2%.
  8. For design aid only, not subject to production testing.

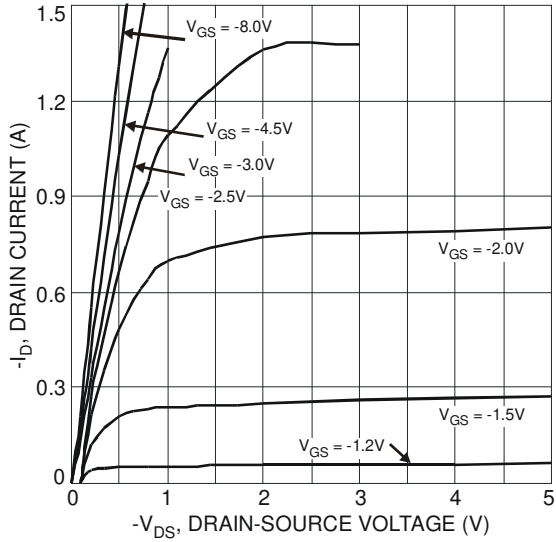


Fig. 1 Typical Output Characteristic

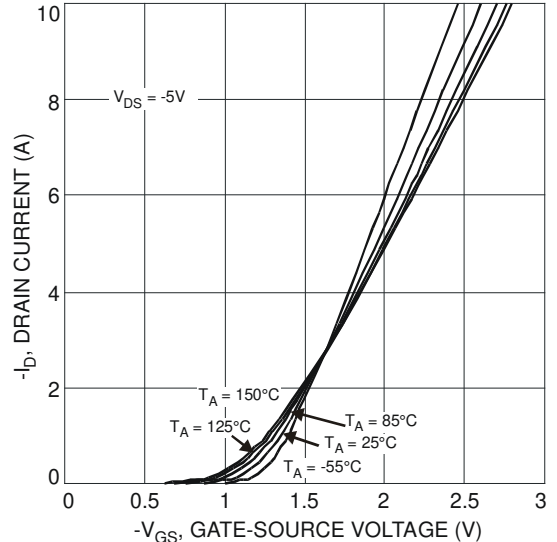


Fig. 2 Typical Transfer Characteristic

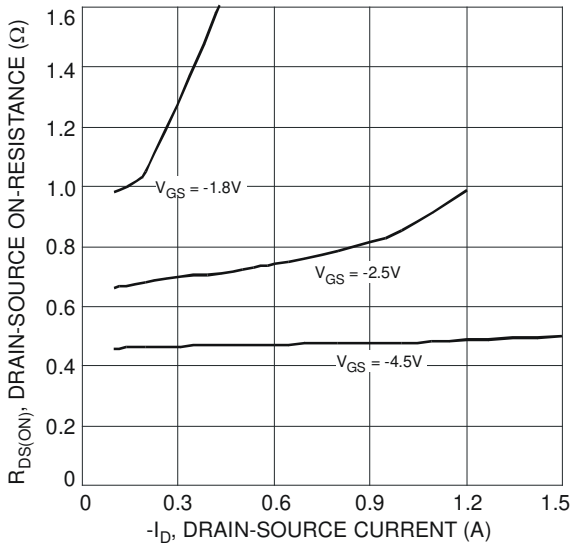


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

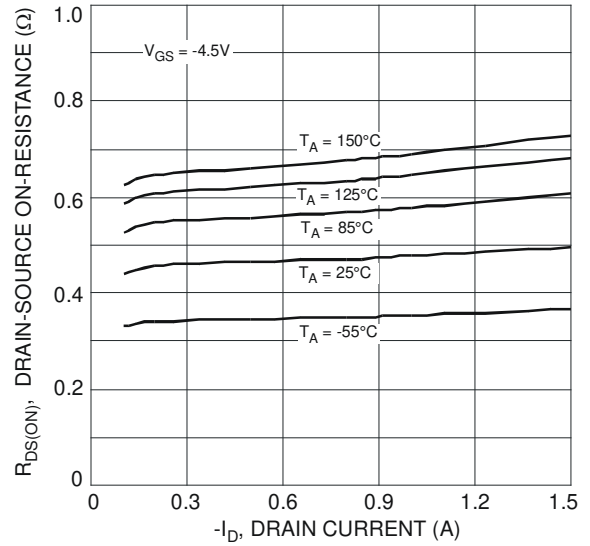


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

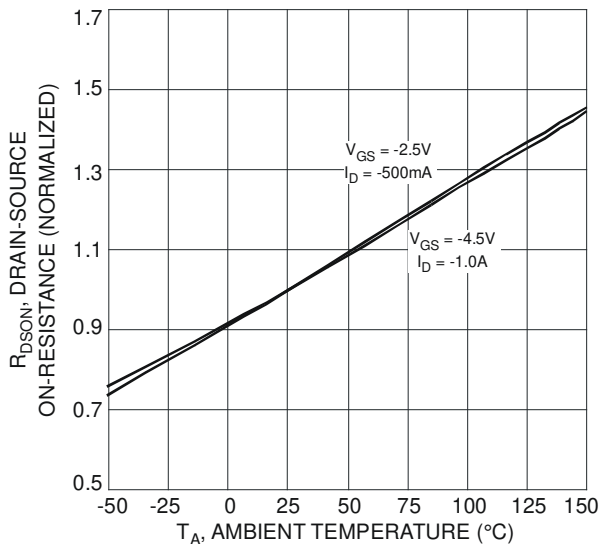


Fig. 5 On-Resistance Variation with Temperature

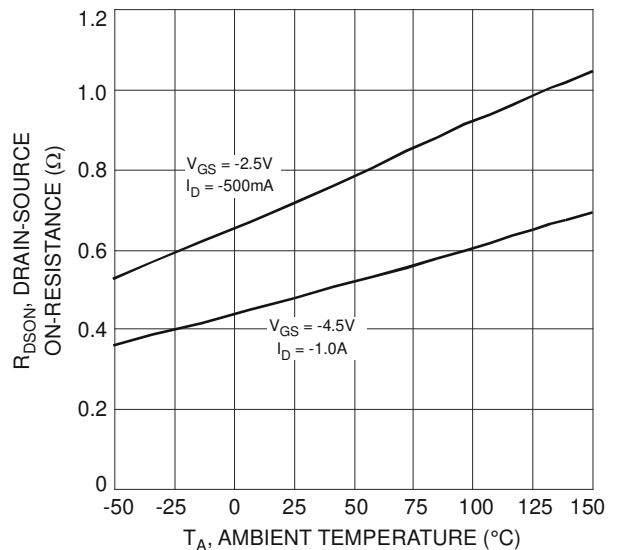


Fig. 6 On-Resistance Variation with Temperature

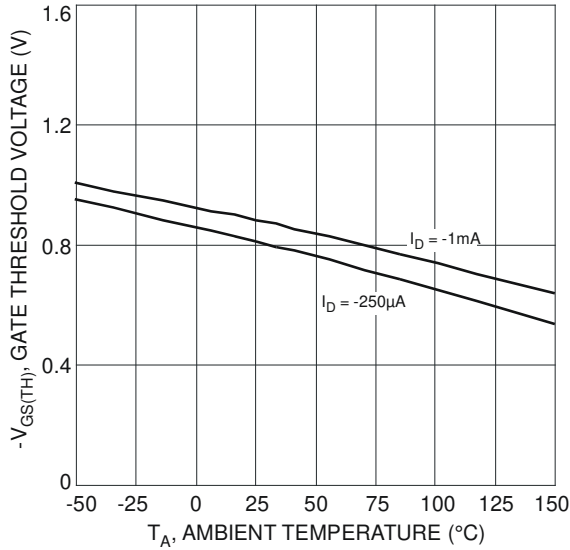


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

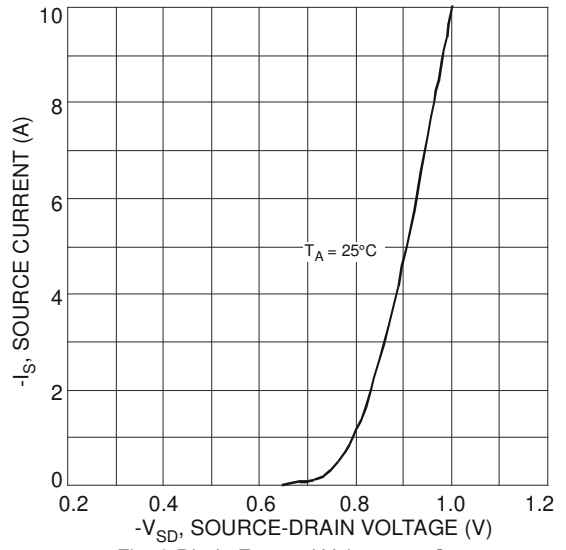


Fig. 8 Diode Forward Voltage vs. Current

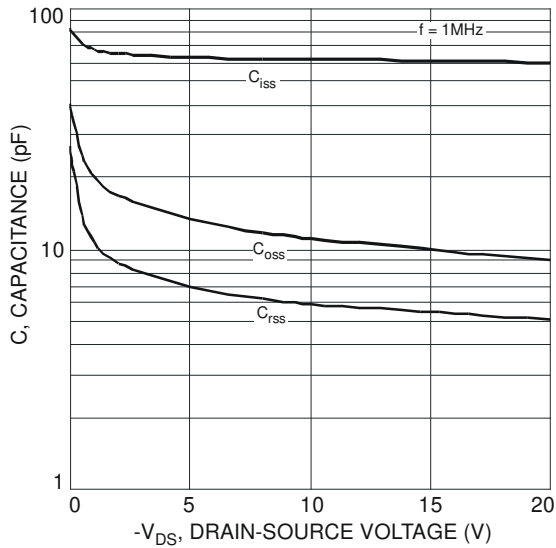


Fig. 9 Typical Total Capacitance

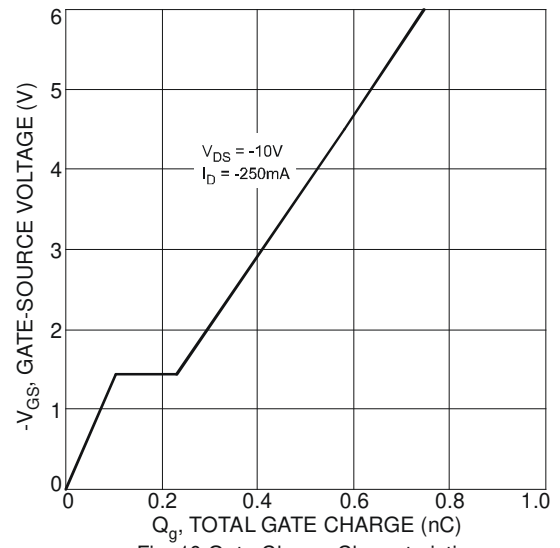


Fig. 10 Gate-Charge Characteristics

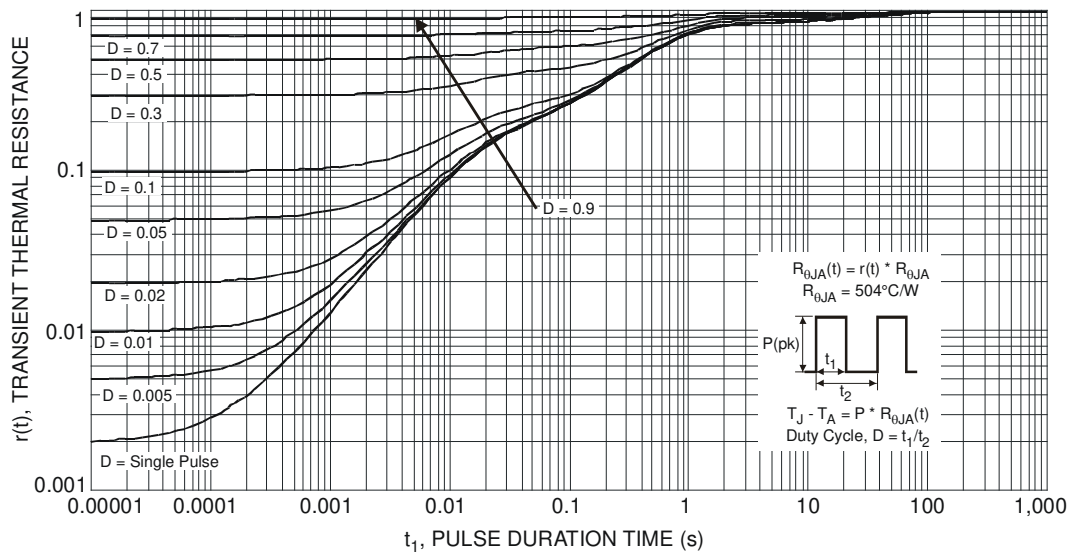
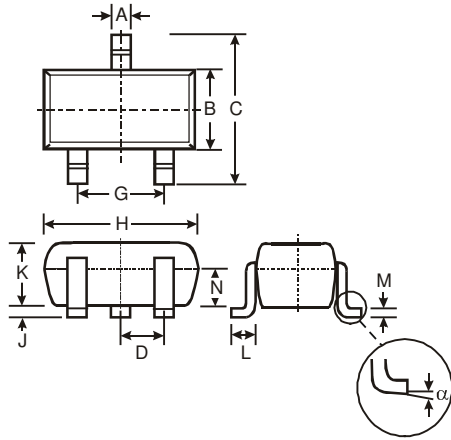


Fig. 11 Transient Thermal Response

**Package Outline Dimensions**

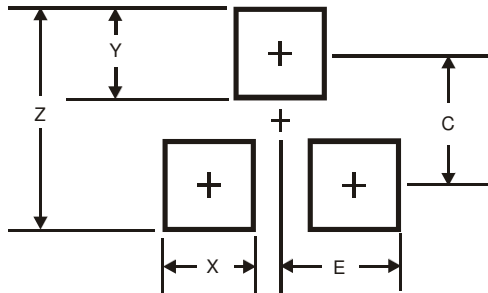
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.



Dimensions	Value (in mm)
Z	1.8
X	0.4
Y	0.51
C	1.3
E	0.7

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